

# DATA SHEET

# NEC

## BIPOLAR ANALOG INTEGRATED CIRCUITS

# $\mu$ PC2745T, $\mu$ PC2749T

### 3V-BIAS, 2.7 GHz/2.9 GHz WIDE-BAND SIMMIC AMPLIFIER FOR MOBILE COMMUNICATIONS

#### DESCRIPTION

$\mu$ PC2745T and  $\mu$ PC2749T are silicon monolithic integrated circuits designed as buffer amplifiers for mobile communications. These ICs feature 3V bias supply and 2.7 or 2.9 GHz wide band operation. 3 V supply operation is suitable for low voltage systems. 2.7 GHz or 2.9 GHz wide band operation is applicable for not only cellular/cordless telephones but also wireless LAN and so on. Due to the 50  $\Omega$  cascadable and mini-mold package, these ICs are suitable for high-density surface mounting.

These ICs are manufactured using NEC's 20 GHz f<sub>T</sub> NESAT™ III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, this series have excellent performance, uniformity and reliability.

#### FEATURES

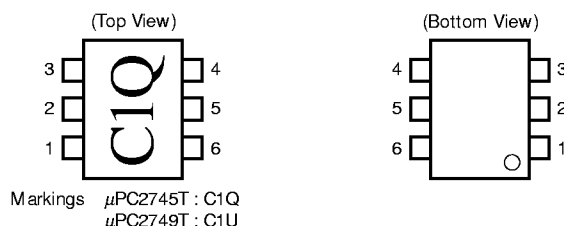
- Recommended supply voltage :  $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$   
(minimum operation voltage :  $\mu$ PC2745T -  $V_{CC} = 1.8 \text{ V}$ ,  $\mu$ PC2749T -  $V_{CC} = 2.7 \text{ V}$ )
- Wide band operation :  $\mu$ PC2745T -  $G_P = 12 \text{ dB}$ ,  $f_u = 2.7 \text{ GHz}$   
 $\mu$ PC2749T -  $G_P = 16 \text{ dB}$ ,  $f_u = 2.9 \text{ GHz}$
- Noise Figure :  $\mu$ PC2745T -  $NF = 6.0 \text{ dB @ } 0.5 \text{ GHz}$ ,  $NF = 5.5 \text{ dB @ } 1.0 \text{ GHz}$   
 $\mu$ PC2749T -  $NF = 3.2 \text{ dB @ } 0.9 \text{ GHz}$ ,  $NF = 4.0 \text{ dB @ } 1.9 \text{ GHz}$
- Isolation :  $\mu$ PC2745T -  $ISL = 38 \text{ dB @ } 0.5 \text{ GHz}$   
 $\mu$ PC2749T -  $ISL = 30 \text{ dB @ } 1.9 \text{ GHz}$
- 50  $\Omega$  cascadable : 50  $\Omega$  input/output impedance
- High-density surface mounting : 6 pin mini mold package

#### OPERING INFORMATION

PART NUMBER	PACKAGE	SUPPLYING FORM
$\mu$ PC2745T-E3 $\mu$ PC2749T-E3	6 pin mini mold	Embossed tape 8 mm wide. Pin 1, 2, 3 face to perforation side of the tape. QTY 3 kp/reel.

**Caution** To order evaluation samples, please contact your local NEC sales office. (Part number:  $\mu$ PC2745T,  $\mu$ PC2749T)

#### PIN CONNECTION



Pin No	Pin name
1	Input
2	GND
3	GND
4	Output
5	GND
6	V <sub>CC</sub>

**Caution** Electro-static sensitive devices

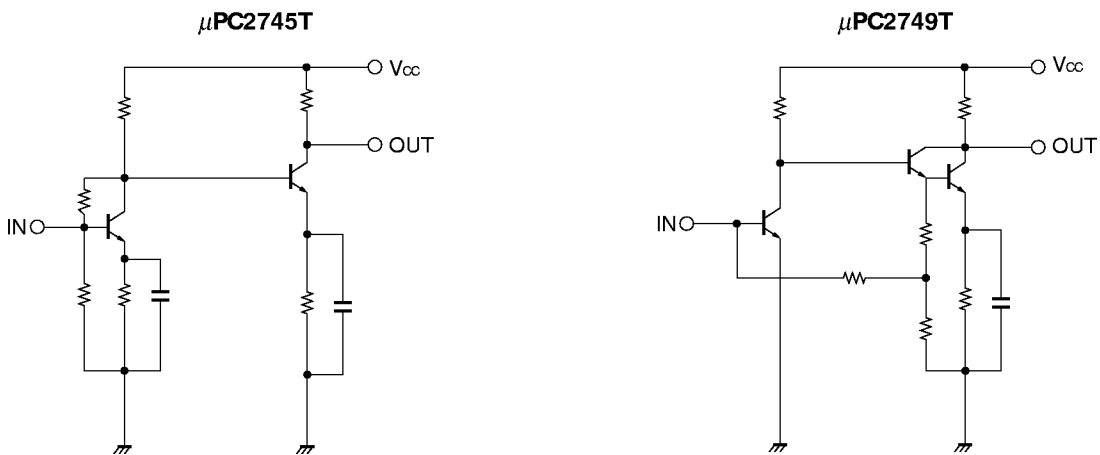
The information in this document is subject to change without notice.

**Selector Guide** ( $T_A = +25\text{ }^\circ\text{C}$ ,  $Z_L = Z_S = 50\ \Omega$ )

TYPE	PART NUMBER	V <sub>cc</sub> (V)	I <sub>cc</sub> (mA)	G <sub>P</sub> (dB)	f <sub>u</sub> (GHz)	NF (dB)	ISL (dB)	P <sub>O(sat)</sub> (dBm)
5 V, 13 dB gain	$\mu$ PC2711T	4.5 - 5.5	12	13	2.9	5.0	30	+1
5 V, 20 dB gain	$\mu$ PC2712T	4.5 - 5.5	12	20	2.6	4.5	33	+3
3 V, 13 dB gain	$\mu$ PC2745T	(1.8 -) 2.7 - 3.3	7.5	12	2.7	6.0	38	-1
3 V, 16 dB gain	$\mu$ PC2749T	2.7 - 3.3	6	16	2.9	4.0	30	-6

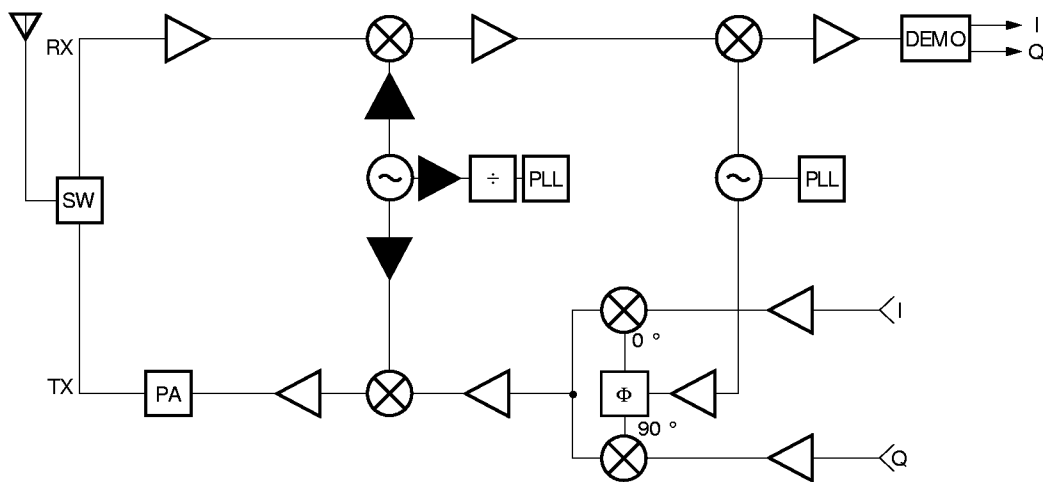
**Note 1** Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

**EQUIVALENT CIRCUITS**



**SYSTEM APPLICATION EXAMPLE**

**Digital cellular telephone**



▶ :  $\mu$ PC2745T,  $\mu$ PC2749T

This system diagram presents schematic application only of these ICs. Suitable IC and block can be chosen in accordance with required RF performance on customer's systems.

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	RATING	UNIT	CONDITIONS
Supply Voltage	V <sub>cc</sub>	4.0	V	T <sub>A</sub> = +25 °C
Circuit Current	I <sub>cc</sub>	15 <b>Note 2</b>	mA	T <sub>A</sub> = +25 °C
Power Dissipation	P <sub>D</sub>	280	mW	Mounted on 50 × 50 × 1.6 mm double side copper clad epoxy glass PWD T <sub>A</sub> = +85 °C
Operating Temperature	T <sub>A</sub>	-40 to +85	°C	
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C	
Input Power	P <sub>in</sub>	0	dBm	T <sub>A</sub> = +25 °C

**Note 2**  $\mu$ PC2745T: 16 mA

**RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	MN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>cc</sub>	2.7	3.0	3.3	V
Operating Temperature	T <sub>A</sub>	-40	+25	+85	°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25 °C, V<sub>cc</sub> = 3.0 V, Z<sub>L</sub> = Z<sub>s</sub> = 50 Ω)**

PARAMETER	SYMBOL	$\mu$ PC2745T			$\mu$ PC2749T			UNIT	CONDITION
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Circuit Current	I <sub>cc</sub>	5.0	7.5	10.0	4	6	8	mA	No input signals
Power Gain	G <sub>p</sub>	9.0	12	14	13	16	18.5	dB	<b>Note 3</b>
Noise Figure	NF		6	7.5		4.0	5.5	dB	<b>Note 3</b>
Upper Limit Operating Frequency	f <sub>u</sub>	2.3	2.7		2.5	2.9		GHz	3 dB less than the gain at 0.1 GHz
Isolation	ISL	33	38		25	30		dB	<b>Note 3</b>
Input Return Loss	RL <sub>in</sub>	8	11		7	10		dB	<b>Note 3</b>
Output Return Loss	RL <sub>out</sub>	2.5	5.5		9.5	12.5		dB	<b>Note 3</b>
Saturated output power	P <sub>O(sat)</sub>	-4	-1		-9	-6		dBm	<b>Note 3</b> P <sub>in</sub> = -6 dBm

**Note 3** Specified frequency condition:  $\mu$ PC2745T – f = 500 MHz,  $\mu$ PC2749T – f = 1.9 GHz

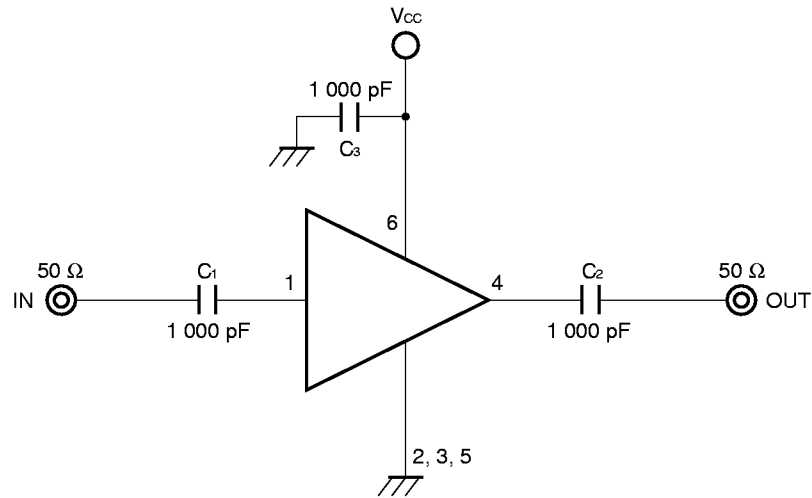
**STANDARD CHARACTERISTICS FOR REFERENCE (T<sub>A</sub> = +25 °C, Z<sub>L</sub> = Z<sub>s</sub> = 50 Ω)**

PARAMETER	SYMBOL	CONDITION	$\mu$ PC2745T	UNIT
			REFERENCE VALUE	
Circuit Current	I <sub>cc</sub>	V <sub>cc</sub> = 1.8 V, No input signals	4.5	mA
Power Gain	G <sub>p</sub>	V <sub>cc</sub> = 3.0 V, f = 1 GHz	12	dB
		V <sub>cc</sub> = 3.0 V, f = 2 GHz	11	
		V <sub>cc</sub> = 1.8 V, f = 500 MHz	7	
Noise Figure	NF	V <sub>cc</sub> = 3.0 V, f = 1 GHz	5.5	dB
		V <sub>cc</sub> = 3.0 V, f = 2 GHz	5.7	
		V <sub>cc</sub> = 1.8 V, f = 500 MHz	8.0	
Upper Limit Operating Frequency	f <sub>u</sub>	V <sub>cc</sub> = 1.8 V, 3 dB less than the gain at 0.1 GHz	1.8	GHz
Isolation	ISL	V <sub>cc</sub> = 3.0 V, f = 1 GHz	33	dB
		V <sub>cc</sub> = 3.0 V, f = 2 GHz	30	
		V <sub>cc</sub> = 1.8 V, f = 500 MHz	35	
Input Return Loss	RL <sub>in</sub>	V <sub>cc</sub> = 3.0 V, f = 1 GHz	13	dB
		V <sub>cc</sub> = 3.0 V, f = 2 GHz	14	
		V <sub>cc</sub> = 1.8 V, f = 500 MHz	6.5	
Output Return Loss	RL <sub>out</sub>	V <sub>cc</sub> = 3.0 V, f = 1 GHz	6.5	dB
		V <sub>cc</sub> = 3.0 V, f = 2 GHz	8.5	
		V <sub>cc</sub> = 1.8 V, f = 500 MHz	6.0	
Saturated Output Power	P <sub>O(sat)</sub>	V <sub>cc</sub> = 3.0 V, f = 1 GHz, P <sub>in</sub> = -6 dBm	-2.5	dBm
		V <sub>cc</sub> = 3.0 V, f = 2 GHz, P <sub>in</sub> = -6 dBm	-3.5	
		V <sub>cc</sub> = 1.8 V, f = 500 MHz, P <sub>in</sub> = -10 dBm	-11	
3rd Order Intermodulation Distortion	IM <sub>3</sub>	V <sub>cc</sub> = 3.0 V, P <sub>out</sub> = -20 dBm, f <sub>1</sub> = 500 MHz, f <sub>2</sub> = 502 MHz	-54	dBc
		V <sub>cc</sub> = 3.0 V, P <sub>out</sub> = -20 dBm, f <sub>1</sub> = 1000 MHz, f <sub>2</sub> = 1002 MHz	-50	
		V <sub>cc</sub> = 1.8 V, P <sub>out</sub> = -20 dBm, f <sub>1</sub> = 500 MHz, f <sub>2</sub> = 502 MHz	-31	

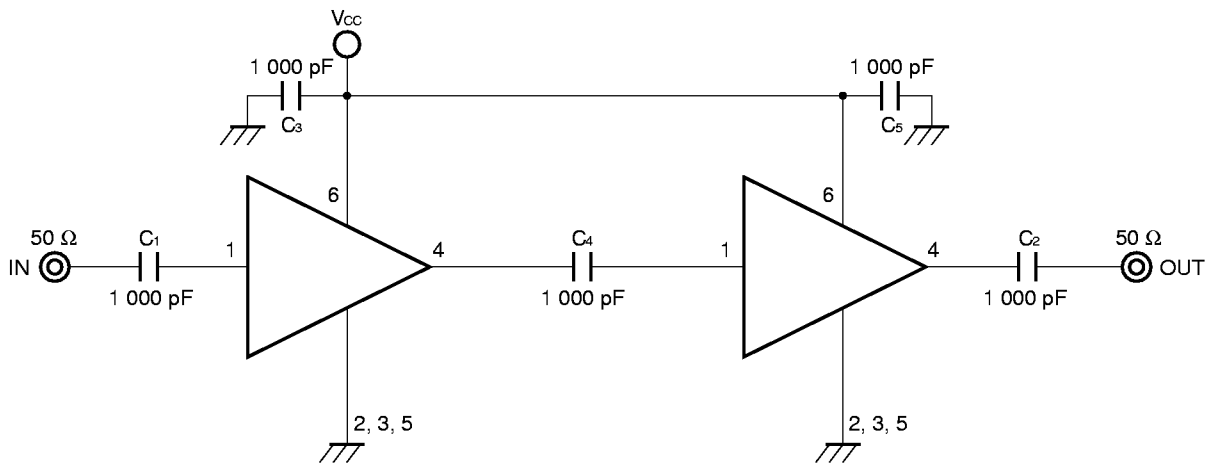
**STANDARD CHARACTERISTICS FOR REFERENCE (T<sub>A</sub> = +25 °C, V<sub>cc</sub> = 3.0 V, Z<sub>L</sub> = Z<sub>s</sub> = 50 Ω)**

PARAMETER	SYMBOL	CONDITION	$\mu$ PC2749T	UNIT
			REFERENCE VALUE	
1 dB compression output	P <sub>O(1dB)</sub>	f = 1.9 GHz	-12.5	dBm
3rd Order Intermodulation Distortion	IM <sub>3</sub>	P <sub>out</sub> = -25 dBm, f <sub>1</sub> = 1.9 GHz, f <sub>2</sub> = 1.902 GHz	-43	dBc
Power Gain	G <sub>p</sub>	f = 0.9 GHz	14.5	dB
Noise Figure	NF	f = 0.9 GHz	3.2	dB

TEST CIRCUIT



EXAMPLE OF APPLICATION CIRCUIT



The application circuit and their parameters are for references only and are not intended for use in actual design-in's

**Capacitors for Vcc, input and output pins**

1 000 pF capacitors are recommendable as bypass capacitor for Vcc pin and coupling capacitors for input/output pins.

Bypass capacitor for Vcc pin is intended to minimize Vcc pin's ground impedance. Therefore, stable bias can be supplied against Vcc fluctuation.

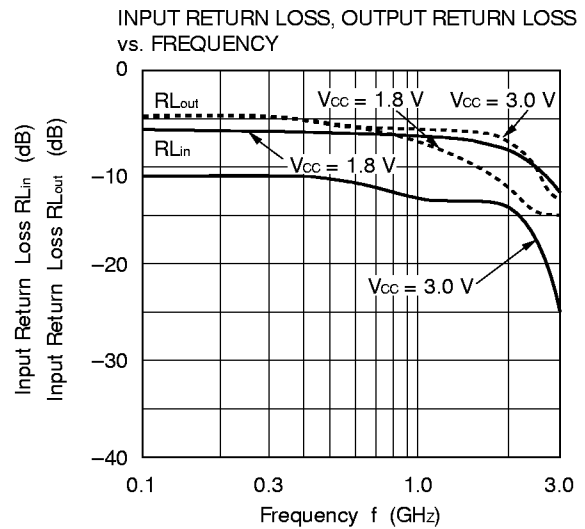
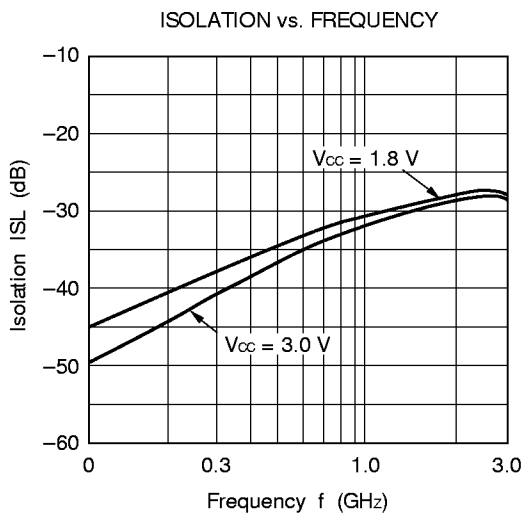
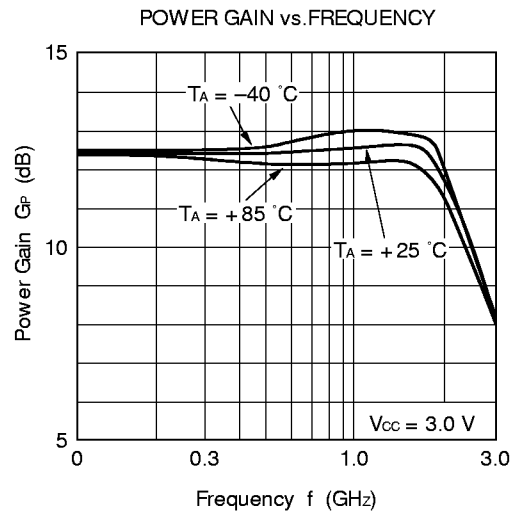
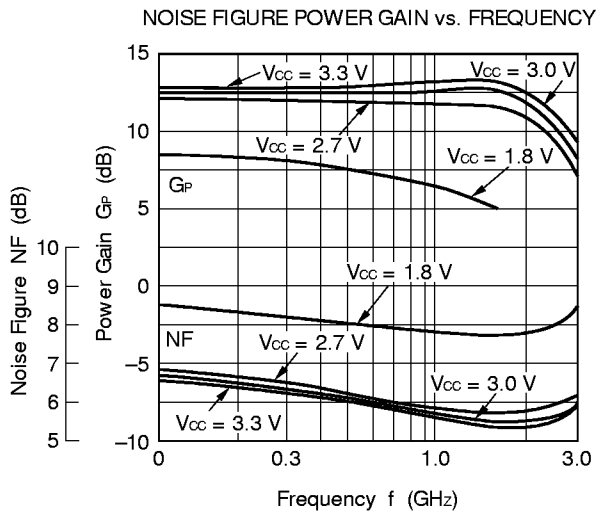
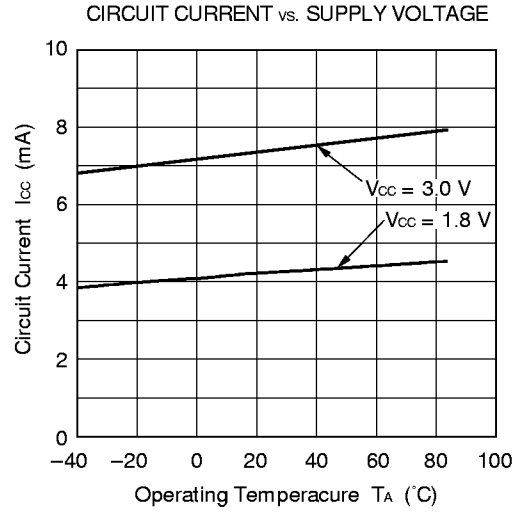
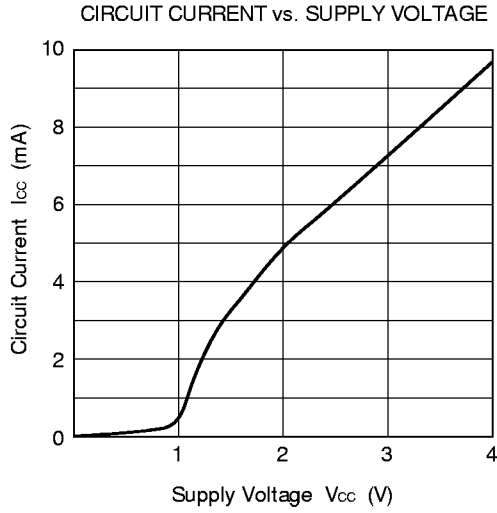
Coupling capacitors for input/output pins are intended to minimize RF serial impedance and cut DC.

To get flat gain from 100 MHz up, 1 000 pF capacitors are assembled on the test circuit. [Actually, 1000 pF capacitors give flat gain at least 10 MHz. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 2 200 pF. Because the coupling capacitors are determined by the equation of

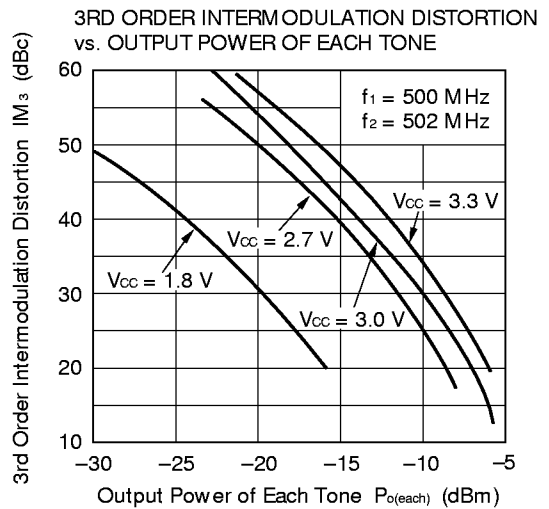
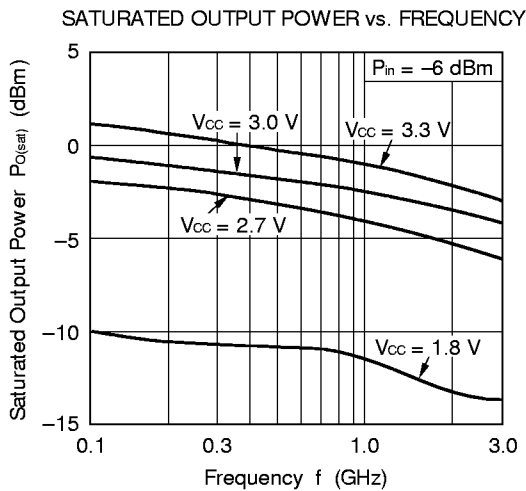
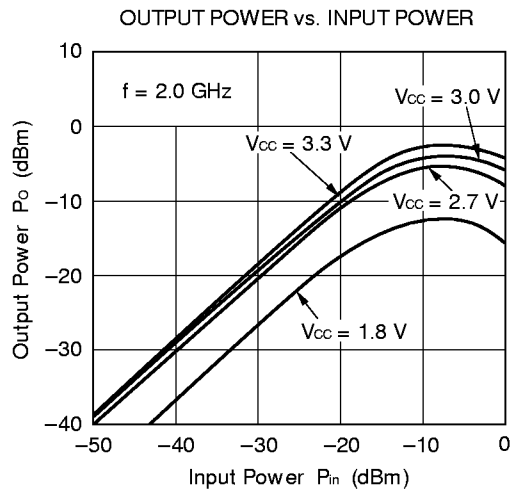
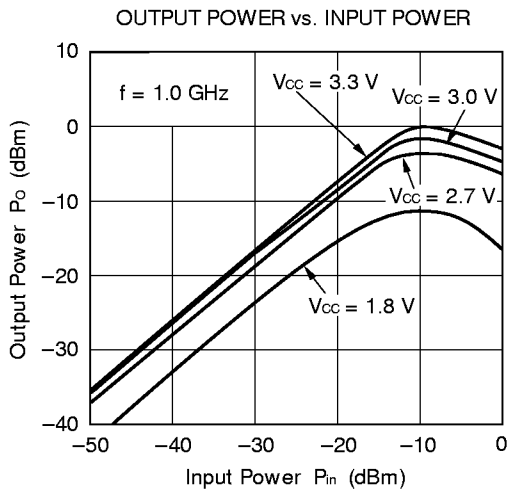
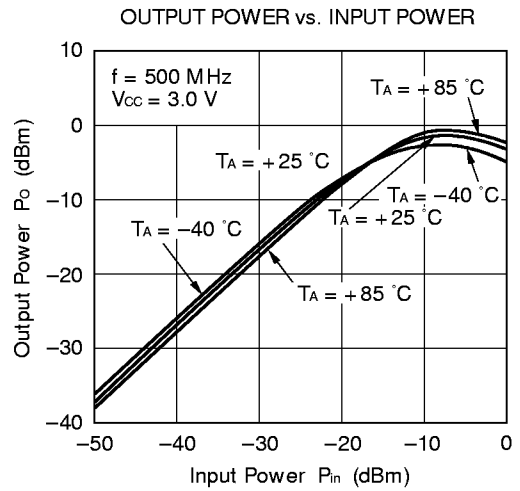
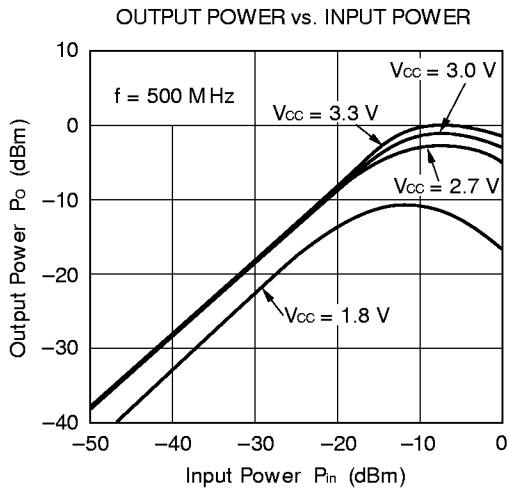
$$C = 1/(2 \pi fZs).]$$

TYPICAL CHARACTERISTICS —  $\mu$ PC2745T —

(Unless otherwise specified,  $T_A = +25^\circ\text{C}$ )



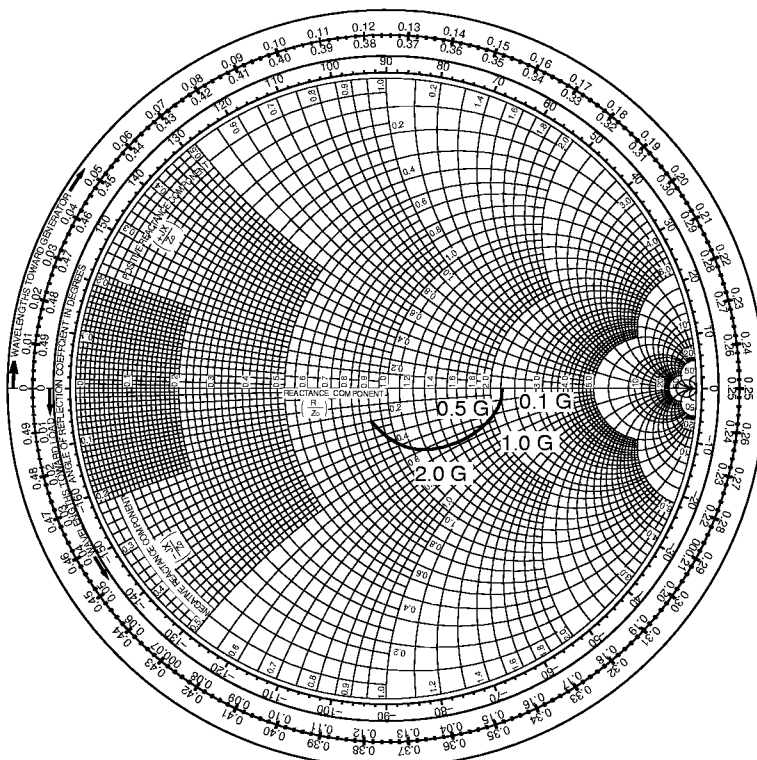
—  $\mu$ PC2745T —



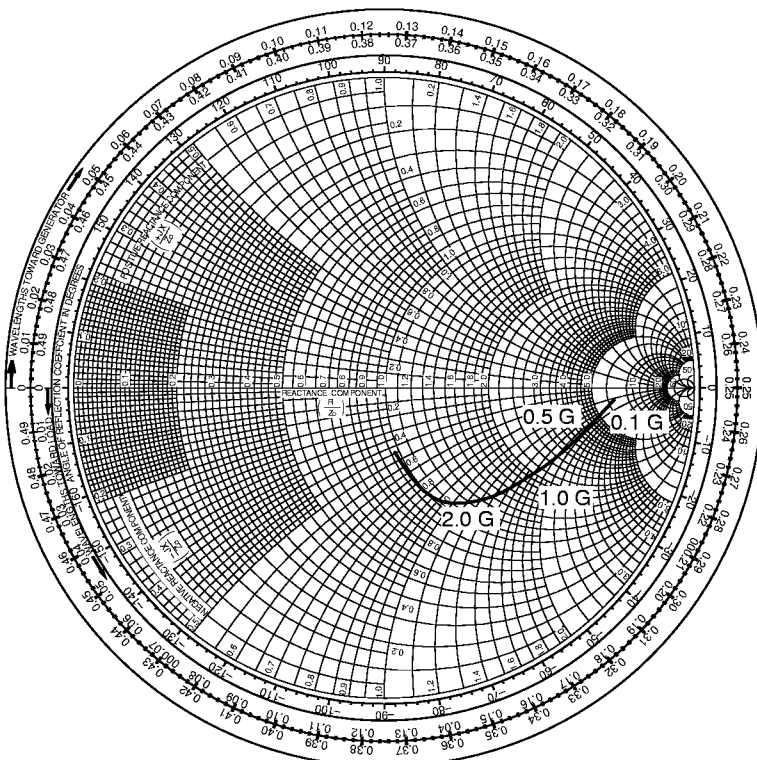
—  $\mu$ PC2745T —

S Parameter ( $V_{cc} = 3.0\text{ V}$ )

S<sub>11</sub>-FREQUENCY

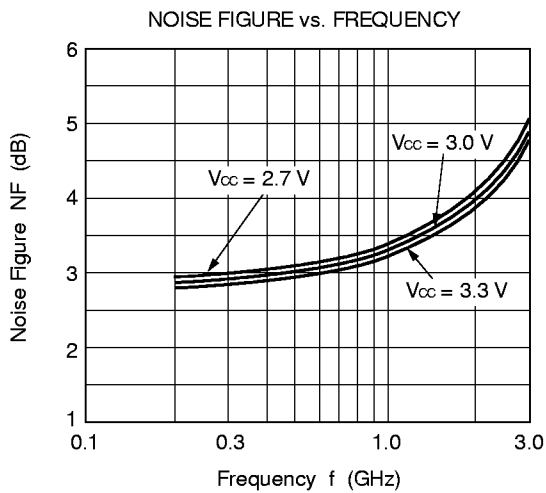
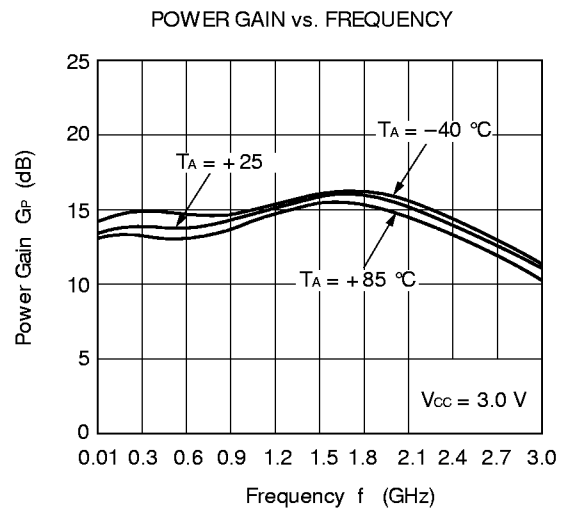
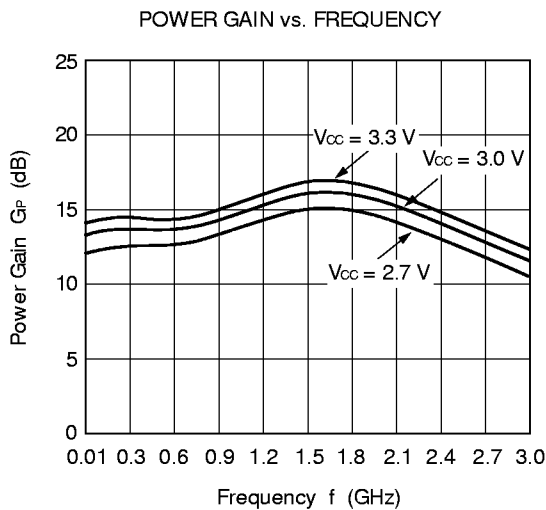
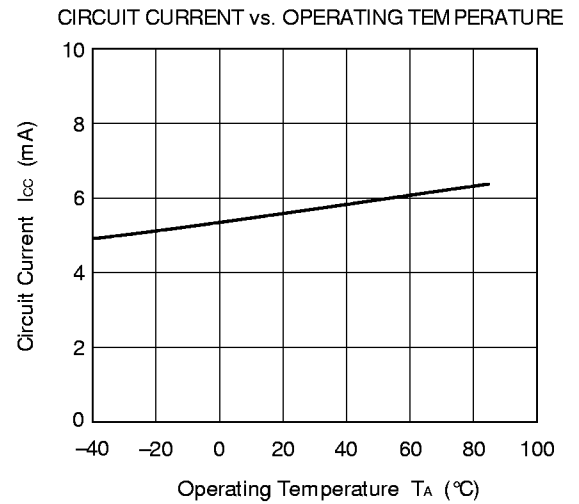
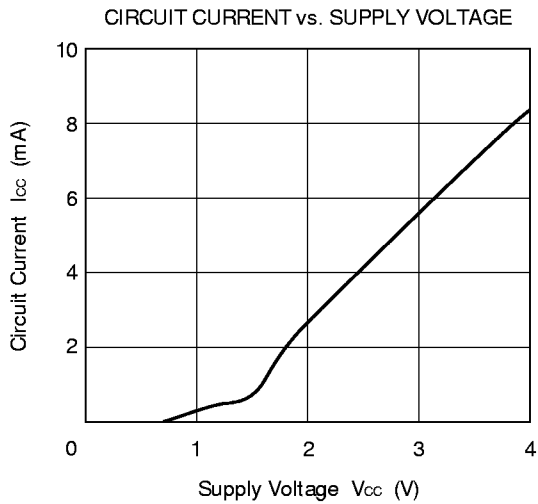


S<sub>22</sub>-FREQUENCY



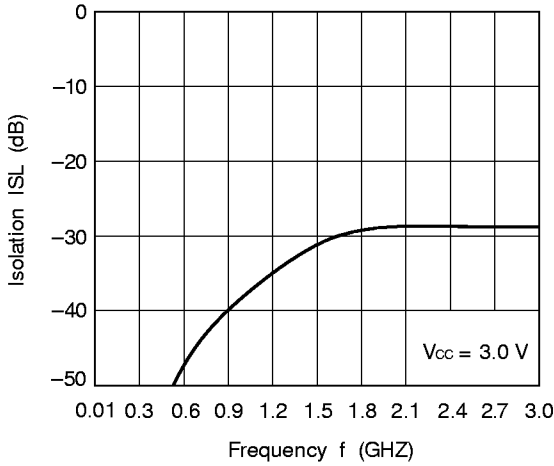
TYPICAL CHARACTERISTICS —  $\mu$ PC2749T —

(Unless otherwise specified,  $T_A = +25\text{ }^\circ\text{C}$ )

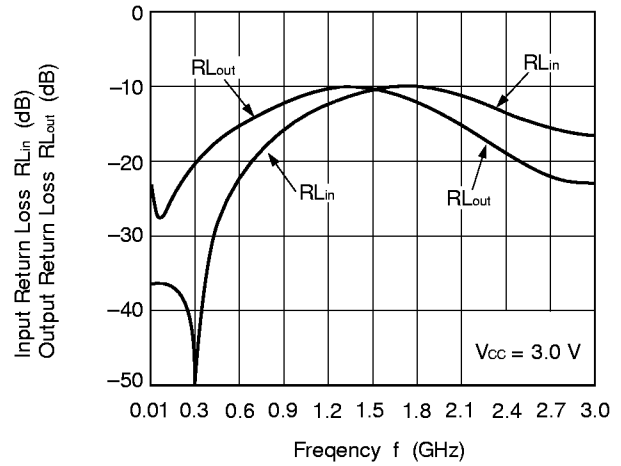


—  $\mu$ PC2749T —

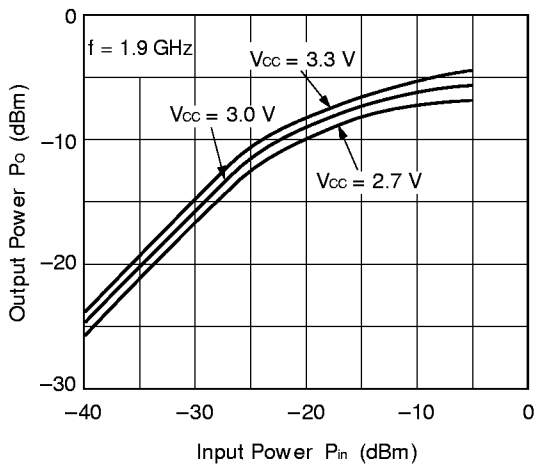
ISOLATION vs. FREQUENCY



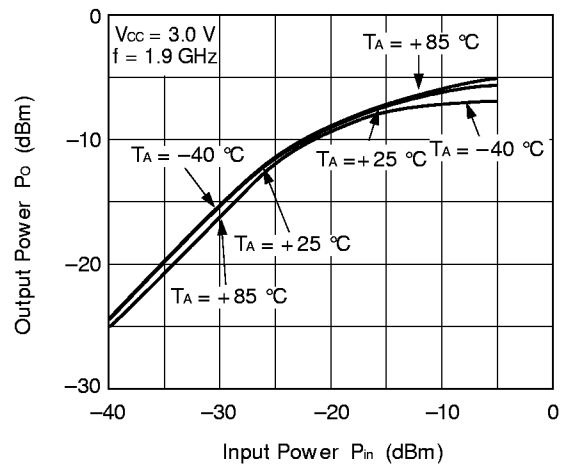
INPUT RETURN LOSS, OUTPUT RETURN LOSS vs. FREQUENCY



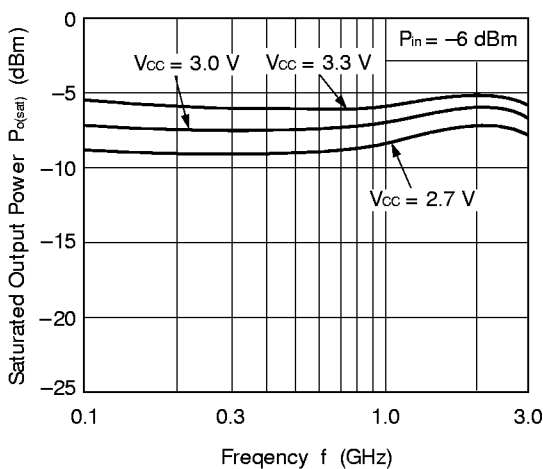
OUTPUT POWER vs. INPUT POWER



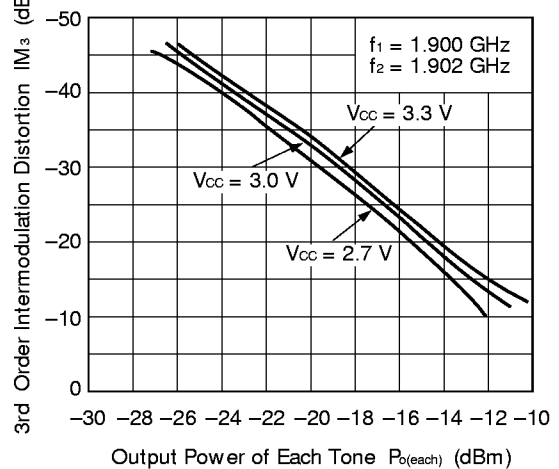
OUTPUT POWER vs. INPUT POWER



SATURATED OUTPUT POWER vs. FREQUENCY



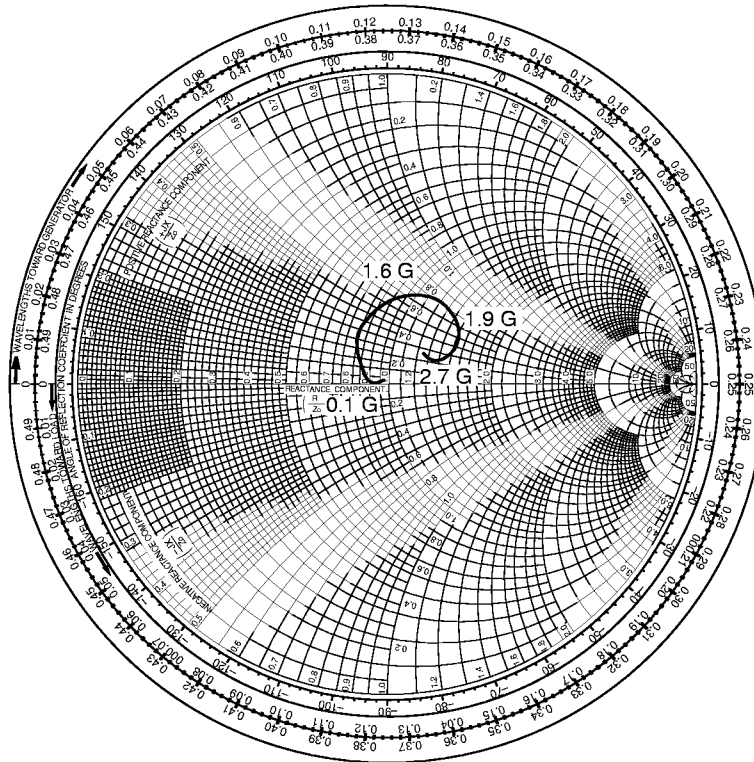
3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE



—  $\mu$ PC2749T —

S Parameter

S<sub>11</sub>-FREQUENCY (V<sub>CC</sub> = 3.0 V)



S<sub>22</sub>-FREQUENCY (V<sub>CC</sub> = 3.0 V)

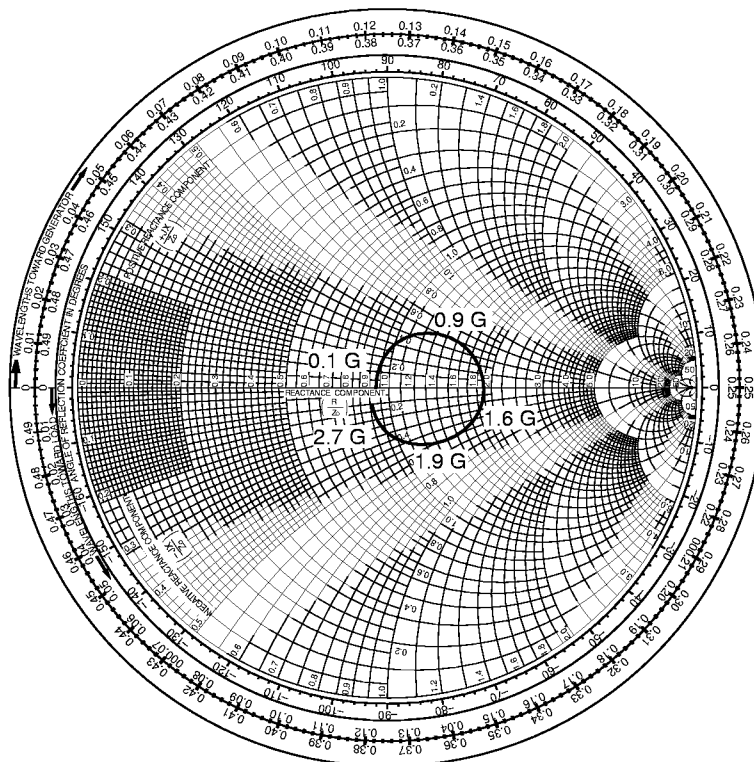
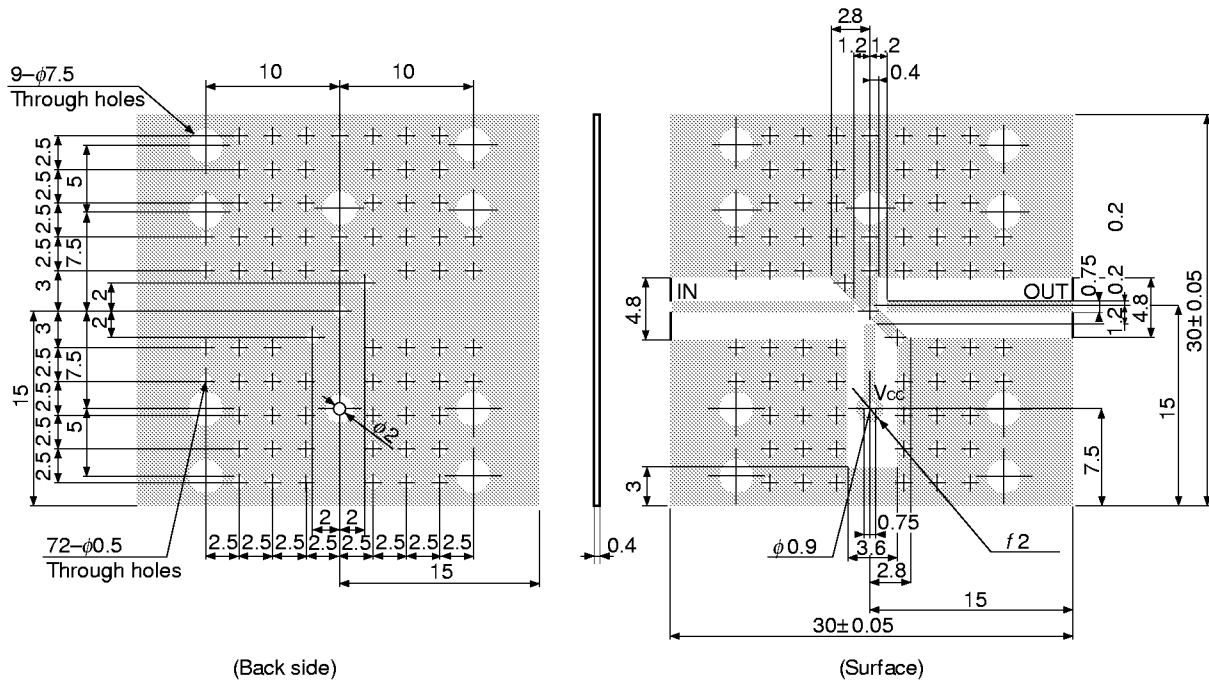


Illustration of evaluation board for the test circuit



Note

- (1) 30 × 30 × 0.4 mm double sided copper clad polyimide board.
- (2) Back side: GND pattern
- (3) Solder plated on pattern
- (4)  $\oplus$  : Through holes

6 PIN MINI MOLD PACKAGE DIMENSIONS (Unit: mm)

